

AMENDMENT TO THE SPECIFICATION:

Please replace paragraph [0015] with the following amended paragraph:

[0015] Therefore, the applicants discovered that with a properly designed flow-channel pattern, desired planarity can be achieved even when the surface topography of the target material as formed is highly ~~[[un-planar]]~~ non-planar. The following exemplary embodiments are for the purpose of describing this invention.

Please replace paragraph [0018] with the following amended paragraph:

[0018] Figure 2 depicts a polishing pad 100, which may be made of material such as polyurethane. Figure 2 also depicts two areas A and B of the polishing pad and the enlargements A' and B' of the two areas, and the flow channels in the areas. Note that the spacing between the flow channels in area A is 'a' and the spacing between the flow channels in area B is 'b'. To polish an outwardly tapered wafer, the more favorable flow-channel pattern for polishing pad should be such that 'a' is wider than 'b' – in some cases, area A may be free of any flow-channels. It is applicants' observation that during the polishing operation, the wafer and the wafer carrier oscillates along a line OP while rotating. As a result, the edge of the wafer travels along the edge of an ellipse E while the center portion of the wafer is confined in the interior of the ellipse E. A flow channel pattern such as depicted in Figure 2 will achieve a polishing rate ~~[[is]]~~ lower at the edge of the wafer because of the more sparsely spaced flow channels at the location A.

Please replace paragraph [0020] with the following amended paragraph:

[0020] Figure 4 depicts another polishing pad and two areas C and D on the polishing pad. Also depicted in Figure 4 are the enlargements C' and D' of the two areas and the flow channels in the areas. The spacing between the flow channels in area C is 'c' and the spacing between the flow-channels in area D is 'd'. To polish an inwardly-tapering wafer, the more favorable flow-channel pattern should be such that 'd' is wider than 'c' – in some cases ~~[[are]]~~ D may be free of any flow-channels. A polishing pad having a flow-channel pattern as depicted in Figure 4 removes the target material more slowly at the center of the wafer because of the more sparsely spaced flow-channels.